TEXAS INSTRUMENTS
Data sheet acquired from Harris Semiconductor
SCHS040D – Revised October 2003

CD4042B Types

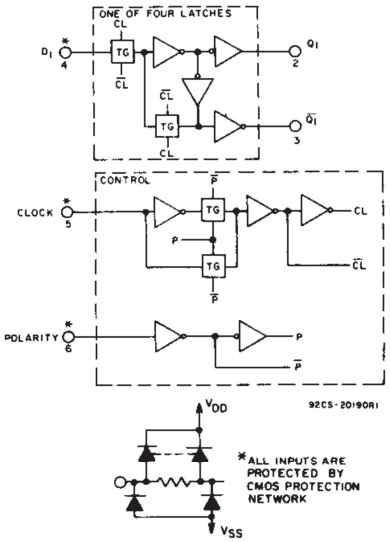
CMOS

Quad Clocked "D" Latch

High-Voltage Types (20-Volt Rating)

■ CD4042B types contain four latch circuits, each strobed by a common clock. Complementary buffered outputs are available from each circuit. The impedance of the n- and p-channel output devices is balanced and all outputs are electrically identical. Information present at the data input is transferred to outputs Q and $\overline{Q}$ during the CLOCK level which is programmed by the POLARITY input. For POLARITY = 0 the transfer occurs during the 0 CLOCK level and for POLARITY = 1 the transfer occurs during the 1 CLOCK level. The outputs follow the data input providing the CLOCK and POLARITY levels defined above are present. When a CLOCK transition occurs (positive for POLARITY = 0 and negative for POLARITY = 1) the information present at the input during the CLOCK transition is retained at the outputs until an opposite CLOCK transition occurs.

The CD4042B types are supplied in 16-lead hermetic dual-in-line ceramic packages (F3A suffixes), 16-lead dual-in-line plastic package (E suffix), 16-lead small-outline packages (D, DR, DT, DW, DWR, and NSR suffixes), and 16-lead thin shrink small-outline packages (PW and PWR suffixes).



CLOCK	POLARITY	Q
0	0	D
⌐	0	LATCH
1	1	D
⌙	1	LATCH

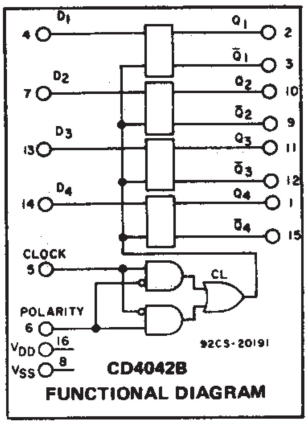
Fig. 1 – Logic block diagram and truth table.

Features:

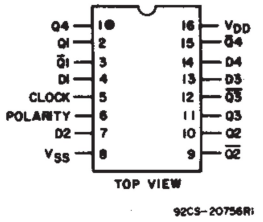
- Clock polarity control
- Q and $\overline{Q}$ outputs
- Common clock
- Low power TTL compatible
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin (over full package temperature range):
  - 1 V at V_{DD} = 5 V
  - 2 V at V_{DD} = 10 V
  - 2.5 V at V_{DD} = 15 V
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

Applications:

- Buffer storage
- Holding register
- General digital logic



FUNCTIONAL DIAGRAM



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	–55	–40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current, I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	–0.64	–0.61	–0.42	–0.36	–0.51	–1	–	
	2.5	0,5	5	–2	–1.8	–1.3	–1.15	–1.6	–3.2	–	
	9.5	0,10	10	–1.6	–1.5	–1.1	–0.9	–1.3	–2.6	–	
	13.5	0,15	15	–4.2	–4	–2.8	–2.4	–3.4	–6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5,4.5	–	5	1.5				–	–	1.5	V
	1,9	–	10	3				–	–	3	
	1.5,13.5	–	15	4				–	–	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current, I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

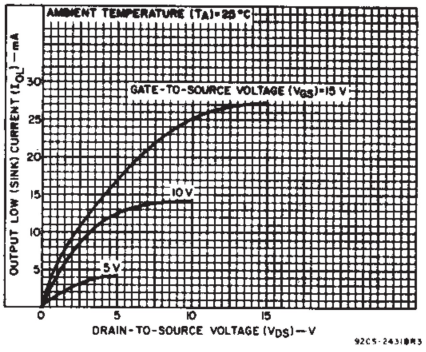


Fig. 2 – Typical output low (sink) current characteristics.

RECOMMENDED OPERATING CONDITIONS at T_A = 25°C, Except as Noted.
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Min.	Max.	
Supply-Voltage Range (For T_A=Full Package Temperature Range)	–	3	18	V
Clock Pulse Width, t_W	5 10 15	200 100 60	– – –	ns
Setup Time, t_S	5 10 15	50 30 25	– – –	ns
Hold Time, t_H	5 10 15	120 60 50	– – –	ns
Clock Rise or Fall Time: t_r , t_f	5,10 15	Not rise or fall time sensitive.		μS

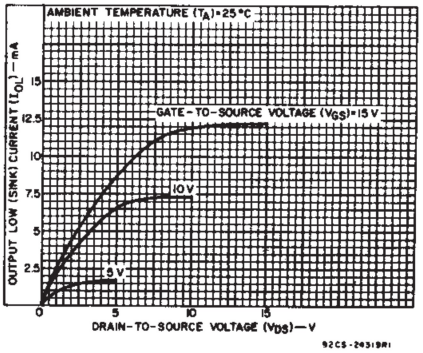


Fig. 3 – Minimum output low (sink) current characteristics.

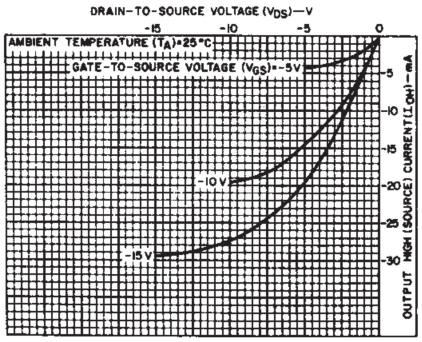


Fig. 4 – Typical output high (source) current characteristics.

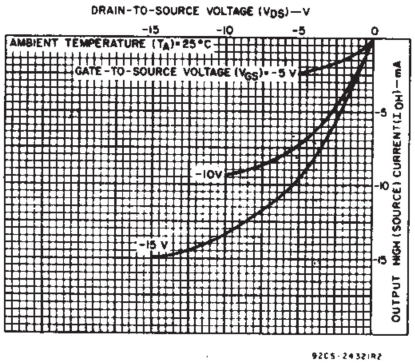


Fig. 5 – Minimum output high (source) current characteristics.

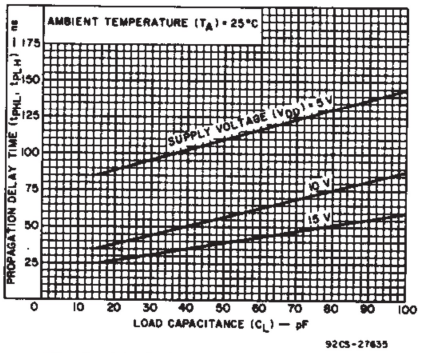


Fig. 6 – Typical propagation delay time vs. load capacitance—data to Q.

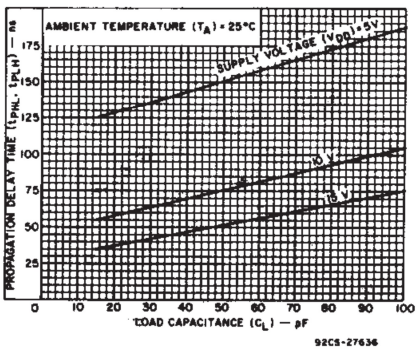


Fig. 7 – Typical propagation delay time vs. load capacitance—data to $\overline{Q}$.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 KΩ

CHARACTERISTIC	V_{DD} (V)	LIMITS		UNITS
		Typ.	Max.	
Propagation Delay Time: t_{PHL}, t_{PLH} Data In to Q	5	110	220	ns
	10	55	110	
	15	40	80	
Data In to $\overline{Q}$	5	150	300	ns
	10	75	150	
	15	50	100	
Clock to Q	5	225	450	ns
	10	100	200	
	15	80	160	
Clock to $\overline{Q}$	5	250	500	ns
	10	115	230	
	15	90	180	
Transition Time : t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Minimum Clock Pulse Width, t_W	5	100	200	ns
	10	50	100	
	15	30	60	
Minimum Hold Time, t_H	5	60	120	ns
	10	30	60	
	15	25	50	
Minimum Setup Time, t_S	5	0	50	ns
	10	0	30	
	15	0	25	
Clock Input Rise or Fall Time: t_r, t_f	5,10	Not rise or fall time sensitive.		μS
	15			
Input Capacitance, C_{IN} Polarity Input	—	5	7.5	pF
All Other Inputs	—	7.5	15	pF

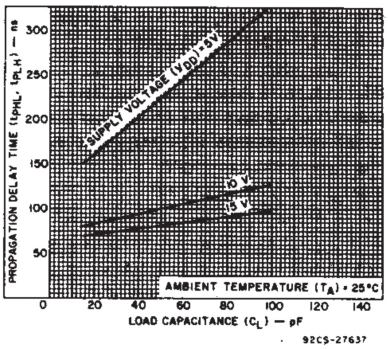


Fig. 8 – Typical propagation delay time vs. load capacitance—clock to Q

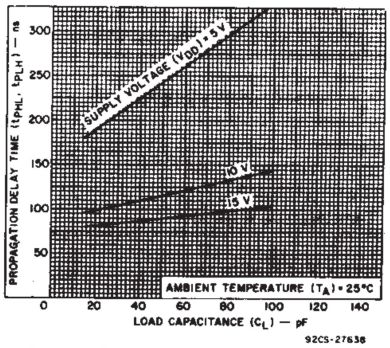


Fig. 9 – Typical propagation delay time vs. load capacitance—clock to $\overline{Q}$.

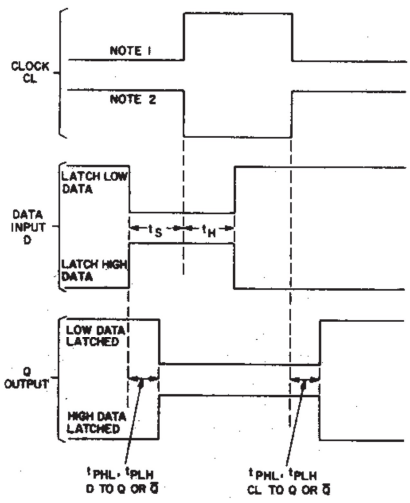


Fig. 12 – Dynamic test parameters.

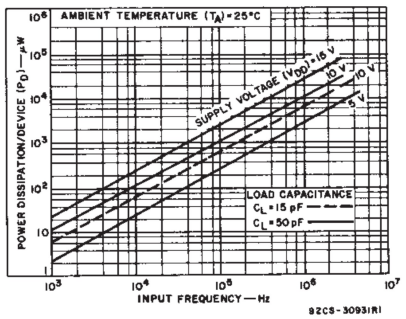


Fig. 10 – Typical power dissipation vs. frequency.

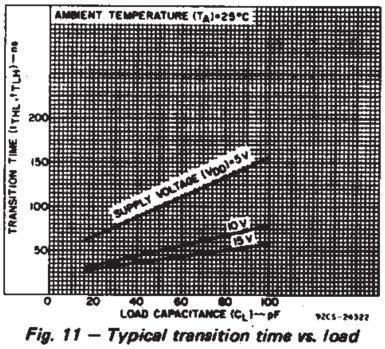


Fig. 11 – Typical transition time vs. load capacitance.

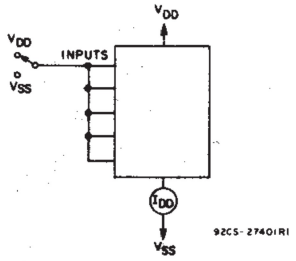


Fig. 13 – Quiescent device current test circuit.

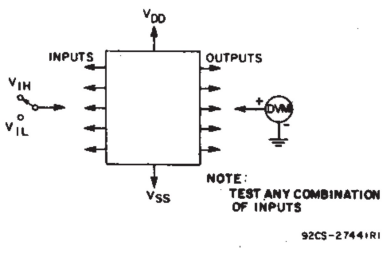


Fig. 14 – Input voltage test circuit.

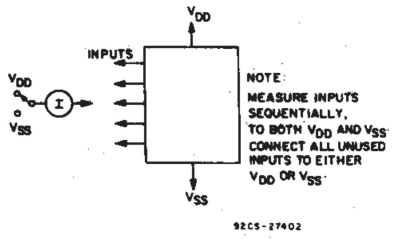
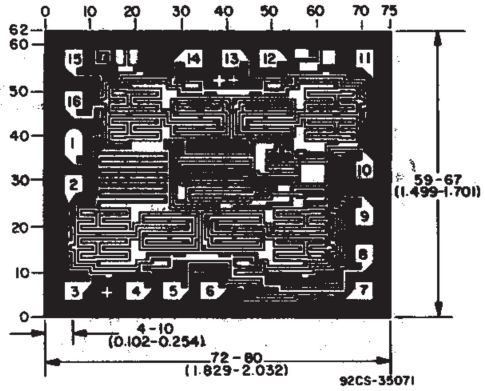


Fig. 15 – Input current test circuit.

Chip Dimensions and Pad Layout



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).